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(71) Applicant *(for all designated States except US)*: **INTEL CORPORATION** [US/US]; 2200 Mission College Boulevard, Santa Clara, CA 95052 (US).

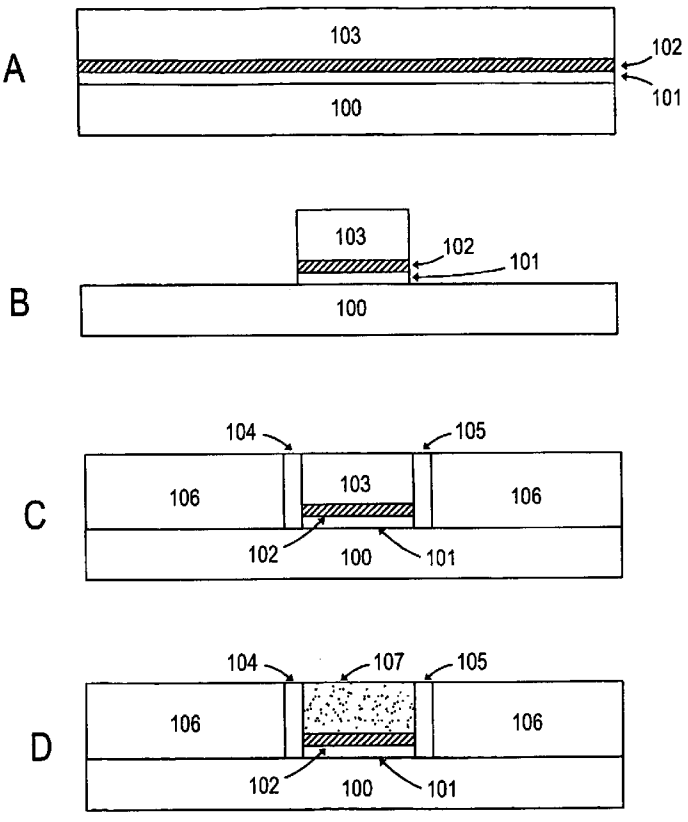
(72) Inventors; and
(75) Inventors/Applicants *(for US only)*: **DOCZY, Mark** [US/US]; 2922 NW Norwalk Place, Beaverton, Oregon 97006 (US). **BRASK, Justin** [US/US]; 12748 NW Bayonne Lane, Portland, Oregon 97229 (US). **KAVALIEROS, Jack** [US/US]; 14260 NW Belle Court, Portland, Oregon 97229 (US). **METZ, Matthew** [US/US]; 3136 NE 13th Ave, Hillsboro, OR 97124 (US). **DATTA, Suman** [IN/US]; 16659 NW Talkingstick Way, Beaverton, Oregon 97006 (US). **CHAU, Robert** [US/US]; 8875 SW 171st Avenue, Beaverton, Oregon 97007 (US).

(74) Agents: **VINCENT, Lester, J.** et al.; BLAKELY SOKOLOFF TAYLOR & ZAFMAN, 12400 Wilshire Boulevard, 7th Floor, Los Angeles, CA 950025 (US).

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(54) Title: A METHOD FOR MAKING A SEMICONDUCTOR DEVICE WITH A HIGH-K GATE DIELECTRIC LAYER AND A SILICIDE GATE ELECTRODE



(57) Abstract: A method for making a semiconductor device is described. That method comprises forming a high-k gate dielectic layer on a substrate, forming a barrier layer on the high-k gate dielectric layer, and forming a fully silicided gate electrode on the barrier layer.

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